Tadeusz Suski

List of Publications by Year
in descending order

342 papers	9,273 citations	66315 42 h-index	53190 85 g-index
344 all docs	344 docs citations	344 times ranked	5248 citing authors

#	Article	IF	Citations
1	Strain-related phenomena in GaN thin films. Physical Review B, 1996, 54, 17745-17753.	1.1	810
2	Observation of Native Ga Vacancies in GaN by Positron Annihilation. Physical Review Letters, 1997, 79, 3030-3033.	2.9	459
3	Lattice parameters of gallium nitride. Applied Physics Letters, 1996, 69, 73-75.	1.5	373
4	Towards the Identification of the Dominant Donor in GaN. Physical Review Letters, 1995, 75, 296-299.	2.9	295
5	Large, nitrogen-induced increase of the electron effective mass in InyGa1â^'yNxAs1â^'x. Applied Physics Letters, 2000, 76, 2409-2411.	1.5	236
6	Pressure Induced Deep Gap State of Oxygen in GaN. Physical Review Letters, 1997, 78, 3923-3926.	2.9	223
7	Thermal expansion of gallium nitride. Journal of Applied Physics, 1994, 76, 4909-4911.	1.1	211
8	Mechanism of yellow luminescence in GaN. Applied Physics Letters, 1995, 67, 2188-2190.	1.5	208
9	Investigation of longitudinalâ€optical phononâ€plasmon coupled modes in highly conducting bulk GaN. Applied Physics Letters, 1995, 67, 2524-2526.	1.5	207
10	Phonon Dispersion Curves in Wurtzite-Structure GaN Determined by Inelastic X-Ray Scattering. Physical Review Letters, 2001, 86, 906-909.	2.9	176
11	Temperature dependence of the energy gap in GaN bulk single crystals and epitaxial layer. Journal of Applied Physics, 1994, 76, 2429-2434.	1.1	171
12	Effect of Si doping on the dislocation structure of GaN grown on the Aâ€face of sapphire. Applied Physics Letters, 1996, 69, 990-992.	1.5	166
13	Pressure studies of gallium nitride: Crystal growth and fundamental electronic properties. Physical Review B, 1992, 45, 13307-13313.	1.1	152
14	Thermal conductivity of GaN crystals in 4.2â€"300 K range. Solid State Communications, 2003, 128, 69-73.	0.9	152
15	Determination of the effective mass of GaN from infrared reflectivity and Hall effect. Applied Physics Letters, 1996, 68, 1114-1116.	1.5	137
16	Influence of indium clustering on the band structure of semiconducting ternary and quaternary nitride alloys. Physical Review B, 2009, 80, .	1.1	132
17	Thermal stability of isolated and complexed Ga vacancies in GaN bulk crystals. Physical Review B, 2001, 64, .	1.1	129
18	High electron mobility in AlGaN/GaN heterostructures grown on bulk GaN substrates. Applied Physics Letters, 2000, 77, 2551-2553.	1.5	119

#	Article	IF	Citations
19	Influence of dopants and substrate material on the formation of Ga vacancies in epitaxial GaN layers. Physical Review B, 2001, 63, .	1.1	104
20	Effect of growth polarity on vacancy defect and impurity incorporation in dislocation-free GaN. Applied Physics Letters, 2005, 86, 031915.	1.5	96
21	Influence of pressure on photoluminescence and electroluminescence in GaN/InGaN/AlGaN quantum wells. Applied Physics Letters, 1997, 70, 2993-2995.	1.5	90
22	The influence of Mg doping on the formation of Ga vacancies and negative ions in GaN bulk crystals. Applied Physics Letters, 1999, 75, 2441-2443.	1.5	77
23	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. Applied Physics Letters, 2006, 88, 201111.	1.5	75
24	Piezoelectric field and its influence on the pressure behavior of the light emission from GaN/AlGaN strained quantum wells. Applied Physics Letters, 2001, 79, 1483-1485.	1.5	72
25	Interdiffusion of In and Ga in InGaN quantum wells. Applied Physics Letters, 1998, 73, 1281-1283.	1.5	69
26	Interband optical absorption in free standing layer of Ga0.96In0.04As0.99N0.01. Applied Physics Letters, 2000, 76, 1279-1281.	1.5	68
27	Influence of pressure on the optical properties ofInxGa1â^'xNepilayers and quantum structures. Physical Review B, 2001, 64, .	1.1	68
28	Heat capacity ofÎ±â^'GaN: Isotope effects. Physical Review B, 2005, 72, .	1.1	68
29	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011114.	1.5	66
30	Lattice constants, thermal expansion and compressibility of gallium nitride. Journal Physics D: Applied Physics, 1995, 28, A149-A153.	1.3	65
31	Highly reproducible, stable and multiply regenerated surface-enhanced Raman scattering substrate for biomedical applications. Journal of Materials Chemistry, 2011, 21, 8662.	6.7	65
32	Band structure and optical properties ofInyGa1â^'yAs1â^'xNxalloys. Physical Review B, 2001, 65, .	1.1	63
33	High mobility two-dimensional electron gas in AlGaNâ^•GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 102106.	1.5	56
34	Evidence for localized Si-donor state and its metastable properties in AlGaN. Applied Physics Letters, 1999, 74, 3833-3835.	1.5	54
35	Bowing of the band gap pressure coefficient in InxGa1â^'xN alloys. Journal of Applied Physics, 2008, 103, 033514.	1.1	53
36	Role of the electron blocking layer in the low-temperature collapse of electroluminescence in nitride light-emitting diodes. Applied Physics Letters, 2007, 90, 103507.	1.5	52

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37	The microstructure of gallium nitride monocrystals grown at high pressure. Journal of Crystal Growth, 1996, 169, 235-242.	0.7	51
38	Infrared spectroscopy of Mg-H local vibrational mode in GaN with polarized light. Physical Review B, 2000, 61, 8238-8241.	1.1	48
39	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. Applied Physics Letters, 2014, 104, .	1.5	48
40	Temperature dependence of electrical properties of gallium-nitride bulk single crystals doped with Mg and their evolution with annealing. Journal of Applied Physics, 2001, 89, 7960-7965.	1.1	44
41	Photocurrent spectroscopy as a tool for determining piezoelectric fields inInxGa1â˘'xN/GaNmultiple quantum well light emitting diodes. Physical Review B, 2004, 69, .	1.1	44
42	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	44
43	Decay of stimulated and spontaneous emission in highly excited homoepitaxial GaN. Applied Physics Letters, 2001, 78, 3776-3778.	1.5	43
44	Phase separation in InGaN multiple quantum wells annealed at high nitrogen pressures. Applied Physics Letters, 1999, 75, 3950-3952.	1.5	42
45	Fully-screened polarization-induced electric fields in blueâ˘•violet InGaNâ˘•GaN light-emitting devices grown on bulk GaN. Applied Physics Letters, 2005, 87, 041109.	1.5	41
46	High pressure andDXcenters in heavily doped bulk GaAs. Physical Review B, 1989, 40, 4012-4021.	1.1	40
47	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. Materials Research Society Symposia Proceedings, 1995, 395, 351.	0.1	40
48	X-ray absorption, glancing-angle reflectivity, and theoretical study of the N K- and GaM2,3-edge spectra in GaN. Physical Review B, 1997, 55, 2612-2622.	1.1	40
49	Thermal stability of in-grown vacancy defects in GaN grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2006, 99, 066105.	1.1	40
50	Doping of Homoepitaxial GaN Layers. Physica Status Solidi (B): Basic Research, 1998, 210, 437-443.	0.7	39
51	Indium incorporation into InGaN and InAlN layers grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2011, 318, 496-499.	0.7	39
52	Influence of GaN substrate offâ€cut on properties of InGaN and AlGaN layers. Crystal Research and Technology, 2012, 47, 321-328.	0.6	39
53	Limitations to band gap tuning in nitride semiconductor alloys. Applied Physics Letters, 2010, 96, .	1.5	38
54	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. Applied Physics Letters, 2007, 91, .	1.5	37

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55	Band Structure and Quantum Confined Stark Effect in InN/GaN superlattices. Crystal Growth and Design, 2012, 12, 3521-3525.	1.4	37
56	GaN homoepitaxial layers grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1999, 75, 1276-1278.	1.5	36
57	High power blueâ€"violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 809-813.	1.0	36
58	Homoepitaxial growth of GaN using molecular beam epitaxy. Journal of Applied Physics, 1996, 80, 2195-2198.	1.1	35
59	Different character of the donor-acceptor pair-related 3.27 eV band and blue photoluminescence in Mg-doped GaN. Hydrostatic pressure studies. Physical Review B, 2000, 62, 10151-10157.	1.1	35
60	Annealing of GaN under high pressure of nitrogen. Journal of Physics Condensed Matter, 2002, 14, 11097-11110.	0.7	35
61	Thermal conductivity of GaN crystals grown by high pressure method. Physica Status Solidi (B): Basic Research, 2003, 240, 447-450.	0.7	35
62	Optical and electrical properties of homoepitaxially grown multiquantum well InGaN/GaN light-emitting diodes. Journal of Applied Physics, 2003, 94, 6122-6128.	1.1	35
63	High-pressure high-temperature annealing of ion-implanted GaN films monitored by visible and ultraviolet micro-Raman scattering. Journal of Applied Physics, 2000, 87, 2736-2741.	1.1	33
64	Graded-index separate confinement heterostructure InGaN laser diodes. Applied Physics Letters, 2013, 103, .	1.5	33
65	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. ACS Photonics, 2019, 6, 1963-1971.	3.2	33
66	Picosecond Z-scan measurements on bulk GaN crystals. Applied Physics Letters, 2001, 78, 4118-4120.	1.5	32
67	Evidence of free carrier concentration gradient along the c-axis for undoped GaN single crystals. Journal of Crystal Growth, 2001, 230, 442-447.	0.7	31
68	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	1.5	31
69	Cavity suppression in nitride based superluminescent diodes. Journal of Applied Physics, 2012, 111, 083106.	1.1	31
70	Theoretical study of the composition pulling effect in InGaN metalorganic vapor-phase epitaxy growth. Japanese Journal of Applied Physics, 2017, 56, 078003.	0.8	31
71	Theoretical study of nitride short period superlattices. Journal of Physics Condensed Matter, 2018, 30, 063001.	0.7	31
72	A pressure-tuned blue-violet InGaN/GaN laser diode grown on bulk GaN crystal. Applied Physics Letters, 2004, 84, 1236-1238.	1.5	30

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73	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. Applied Physics Letters, 2006, 88, 141909.	1.5	30
74	High-nitrogen-pressure growth of GaN single crystals: doping and physical properties. Journal of Physics Condensed Matter, 2001, 13, 8881-8890.	0.7	29
75	Free and bound excitons in GaNâˆ•AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112Â¯0) direction. Applied Physics Letters, 2005, 86, 162112.	1.5	29
76	Band gap bowing in quaternary nitride semiconducting alloys. Applied Physics Letters, 2011, 98, .	1.5	29
77	Thermal conductivity of heavily doped bulk crystals GaN:O. Free carriers contribution. Materials Research Express, 2015, 2, 085902.	0.8	29
78	Ga vacancies in electron irradiated GaN: introduction, stability and temperature dependence of positron trapping. Physica B: Condensed Matter, 2001, 308-310, 77-80.	1.3	28
79	Size effects in band gap bowing in nitride semiconducting alloys. Physical Review B, 2011, 83, .	1.1	28
80	Role of conduction-band filling in the dependence of InN photoluminescence on hydrostatic pressure. Physical Review B, 2007, 76, .	1.1	27
81	Electronic structure and effective masses of InN under pressure. Journal of Applied Physics, 2008, 104, 013704.	1.1	27
82	Anomalous composition dependence of the band gap pressure coefficients in In-containing nitride semiconductors. Physical Review B, 2010, 81, .	1.1	27
83	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. Physical Review B, 2011, 83, .	1.1	27
84	Search for free holes in InN:Mg-interplay between surface layer and Mg-acceptor doped interior. Journal of Applied Physics, 2009, 105, 123713.	1.1	26
85	Lateral Control of Indium Content and Wavelength of IIIâ€"Nitride Diode Lasers by Means of GaN Substrate Patterning. Applied Physics Express, 2012, 5, 021001.	1.1	26
86	Photoluminescence and pressure effects in short period InN/nGaN superlattices. Journal of Applied Physics, 2013, 113, 123101.	1.1	26
87	Factor group analysis of the Raman spectrum of Pb₅Ge₃O₁₁. Physica Status Solidi (B): Basic Research, 1977, 80, 31-41.	0.7	25
88	Vacancies as compensating centers in bulk GaN: doping effects. Journal of Crystal Growth, 2002, 246, 281-286.	0.7	25
89	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. Scientific Reports, 2015, 4, 4371.	1.6	25
90	GaN Crystals: Growth and Doping Under Pressure. Materials Research Society Symposia Proceedings, 1997, 482, 115.	0.1	24

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91	Effect of hydrogen during growth of quantum barriers on the properties of InGaN quantum wells. Journal of Crystal Growth, 2015, 414, 38-41.	0.7	24
92	Observation of Ga vacancies and negative ions in undoped and Mg-doped GaN bulk crystals. Physica B: Condensed Matter, 1999, 273-274, 33-38.	1.3	23
93	Pressure and composition dependence of the electronic structure ofGaAs1â^'xNx. Physical Review B, 2002, 66, .	1.1	23
94	The Application of High Pressure in Physics and Technology of III-V Nitrides. Acta Physica Polonica A, 2001, 100, 57-109.	0.2	23
95	Polarity dependent properties of GaN layers grown by hydride vapor phase epitaxy on GaN bulk crystals. Physica Status Solidi (B): Basic Research, 2003, 240, 289-292.	0.7	22
96	Determination of built-in electric fields in quaternary InAlGaN heterostructures. Applied Physics Letters, 2003, 82, 1541-1543.	1.5	22
97	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaNâ^•GaN multiple quantum wells on bulk GaN substrates. Journal of Applied Physics, 2005, 97, 103507.	1.1	22
98	Anomalous temperature characteristics of single wide quantum well InGaN laser diode. Applied Physics Letters, 2006, 88, 071121.	1.5	22
99	Deep level transient spectroscopy signatures of majority traps in GaN pâ€"n diodes grown by metal-organic vapor-phase epitaxy technique on GaN substrates. Physica B: Condensed Matter, 2009, 404, 4889-4891.	1.3	22
100	Hydrostatic pressure and strain effects in short period InN/GaN superlattices. Applied Physics Letters, 2012, 101, 092104.	1.5	22
101	Band gap engineering of In(Ga)N/GaN short period superlattices. Scientific Reports, 2017, 7, 16055.	1.6	22
102	New phenomena of low temperature resistivity enhancement in quantum ferroelectric semiconductors. Solid State Communications, 1983, 45, 259-262.	0.9	21
103	Lattice parameters of GaN single crystals, homoepitaxial layers and heteroepitaxial layers on sapphire. Journal of Alloys and Compounds, 1999, 286, 271-275.	2.8	21
104	Effective mass and conduction band dispersion of GaAsN/GaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1078-1081.	1.3	21
105	Nitride superluminescent diodes with broadened emission spectrum fabricated using laterally patterned substrate. Optics Express, 2016, 24, 9673.	1.7	21
106	Spatial distribution of electron concentration and strain in bulk GaN single crystals - relation to growth mechanism. Materials Research Society Symposia Proceedings, 1996, 449, 519.	0.1	20
107	Metalâ€Insulator Transition in GaN Crystals. Physica Status Solidi (B): Basic Research, 1996, 198, 223-233.	0.7	20
108	Time-resolved spectroscopy of (Al,Ga,In)N based quantum wells: Localization effects and effective reduction of internal electric fields. Physical Review B, 2002, 66, .	1.1	20

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109	Stimulated emission due to spatially separated electron-hole plasma and exciton system in homoepitaxial GaN. Physical Review B, 2004, 69, .	1.1	20
110	Effect of efficiency â€œdroopâ€•in violet and blue InGaN laser diodes. Applied Physics Letters, 2009, 95, 071108.	1.5	20
111	Different pressure behavior of GaN/AlGaN quantum structures grown along polar and nonpolar crystallographic directions. Journal of Applied Physics, 2009, 105, .	1.1	20
112	Quantum-confined Stark effect and mechanisms of its screening in InGaN/GaN light-emitting diodes with a tunnel junction. Optics Express, 2021, 29, 1824.	1.7	20
113	Growth of AlN, GaN and InN from the solution. International Journal of Materials and Product Technology, 2005, 22, 226.	0.1	19
114	Built-in electric field and large Stokes shift in near-lattice-matched GaNâˆ•AlInN quantum wells. Applied Physics Letters, 2008, 92, .	1.5	19
115	Temperature dependence of superluminescence in InGaN-based superluminescent light emitting diode structures. Journal of Applied Physics, 2010, 108, .	1.1	19
116	Ultralow threshold powers for optical pumping of homoepitaxial InGaN/GaN/AlGaN lasers. Applied Physics Letters, 2002, 81, 3735-3737.	1.5	18
117	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. Applied Physics Letters, 2006, 89, 172119.	1.5	18
118	Influence of internal electric fields on band gaps in short period GaN/GaAlN and InGaN/GaN polar superlattices. Journal of Applied Physics, 2015, 118, .	1.1	18
119	Energy gap in GaN bulk single crystal between 293 and 1237K. Journal of Crystal Growth, 2002, 235, 111-114.	0.7	17
120	Optical gain in homoepitaxial GaN. Applied Physics Letters, 2004, 85, 952-954.	1.5	17
121	Photoreflectance of InN and InN:Mg layers: An evidence of Fermi level shift toward the valence band upon Mg doping in InN. Applied Physics Letters, 2008, 93, 131917.	1.5	17
122	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. Journal of Applied Physics, 2010, 108, 023516.	1.1	17
123	Structural and electronic properties of wurtzite MgZnO and BeMgZnO alloys and their thermodynamic stability. Journal of Applied Physics, 2016, 120, .	1.1	17
124	Blue Laser on High N₂Pressure-Grown Bulk GaN. Acta Physica Polonica A, 2001, 100, 229-232.	0.2	17
125	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. Physica Status Solidi A, 2003, 200, 9-12.	1.7	16
126	Resonant localized donor state above the conduction band minimum in InN. Applied Physics Letters, 2005, 86, 262105.	1.5	16

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127	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. Journal of Applied Physics, 2007, 101, 083109.	1.1	16
128	Inâ€clustering effects in InAlN and InGaN revealed by high pressure studies. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1369-1371.	0.8	16
129	Switching of exciton character in double InGaN/GaN quantum wells. Physical Review B, 2018, 98, .	1.1	16
130	Effect of Si Doping on The Structure of Gan. Materials Research Society Symposia Proceedings, 1996, 423, 487.	0.1	15
131	High pressure fabrication and processing of GaN:Mg. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 1-5.	1.7	15
132	Different pressure coefficients of the light emission in cubic and hexagonal InGaN/GaN quantum wells. Applied Physics Letters, 2002, 81, 232-234.	1.5	15
133	Study of light emission from GaN/AlGaN quantum wells under power-dependent excitation. Journal of Applied Physics, 2002, 91, 9622.	1.1	15
134	Photoconductive Z-scan measurement of multiphoton absorption in GaN. Journal of Applied Physics, 2002, 92, 6930-6932.	1.1	15
135	Optically pumped GaNâˆ•AlGaN separate-confinement heterostructure laser grown along the (112Â¯0) nonpolar direction. Applied Physics Letters, 2007, 90, 081104.	1.5	15
136	Universal behavior of photoluminescence in GaN-based quantum wells under hydrostatic pressure governed by built-in electric field. Journal of Applied Physics, 2012, 112, 053509.	1.1	15
137	Comparison of wurtzite GaN/AlN and ZnO/MgO shortâ€period superlattices: Calculation of band gaps and builtâ€in electric field. Physica Status Solidi (B): Basic Research, 2017, 254, 1600704.	0.7	15
138	High temperature phase transition in Pb5Ge3O11. Physica Status Solidi A, 1976, 35, K165-K167.	1.7	14
139	High pressure investigation of ferroelectric phase transition in PbSnTe. Solid State Communications, 1981, 38, 59-62.	0.9	14
140	Infrared studies on GaN single crystals and homoepitaxial layers. Journal of Crystal Growth, 2000, 218, 161-166.	0.7	14
141	Study of dopant activation in bulk GaN:Mg. Physica B: Condensed Matter, 2001, 308-310, 47-50.	1.3	14
142	Optical and electrical properties of Be doped GaN bulk crystals. Journal of Crystal Growth, 2001, 230, 368-371.	0.7	14
143	High-power laser structures grown on bulk GaN crystals. Journal of Crystal Growth, 2004, 272, 274-277.	0.7	14
144	Band-to-band character of photoluminescence from InN and In-rich InGaN revealed by hydrostatic pressure studies. Applied Physics Letters, 2006, 89, 121915.	1.5	14

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145	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. Applied Physics Letters, 2011, 98, .	1.5	14
146	InGaN laser diodes with reduced AlGaN cladding thickness fabricated on GaN plasmonic substrate. Applied Physics Letters, 2013, 102, .	1.5	14
147	III-nitride optoelectronic devices containing wide quantum wellsâ€"unexpectedly efficient light sources. Japanese Journal of Applied Physics, 2022, 61, SA0801.	0.8	14
148	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>m</mml:mi></mml:math>-plane GaN/AlGaN quantum wells. Physical Review B, 2011, 84, .	1.1	13
149	Band gaps in InN/GaN superlattices: Nonpolar and polar growth directions. Journal of Applied Physics, 2013, 114, 223102.	1.1	13
150	Influence of strain and internal electric fields on band gaps in short period nitride based superlattices. Superlattices and Microstructures, 2015, 82, 438-446.	1.4	13
151	450 nm (Al,In)GaN optical amplifier with double â€˜j-shapeâ€™ waveguide for master oscillator power amplifier systems. Optics Express, 2018, 26, 7351.	1.7	13
152	Modelling the growth of nitrides in ammoniaâ€rich environment. Crystal Research and Technology, 2007, 42, 1281-1290.	0.6	12
153	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1485-1487.	0.8	12
154	Fabrication and properties of GaN-based lasers. Journal of Crystal Growth, 2008, 310, 3979-3982.	0.7	12
155	Tilt of InGaN layers on miscut GaN substrates. Physica Status Solidi - Rapid Research Letters, 2010, 4, 142-144.	1.2	12
156	AlGaInN laser-diode technology for optical clocks and atom interferometry. , 2017, , .		12
157	Reviewâ€"Review on Optimization and Current Status of (Al,In)GaN Superluminescent Diodes. ECS Journal of Solid State Science and Technology, 2020, 9, 015010.	0.9	12
158	Pressure induced phase transition in PbSnTe. Solid State Communications, 1979, 30, 77-80.	0.9	11
159	Blue-Laser Structures Grown on Bulk GaN Crystals. Physica Status Solidi A, 2002, 192, 320-324.	1.7	11
160	Light emission versus energy gap in group-III nitrides: hydrostatic pressure studies. Physica Status Solidi (B): Basic Research, 2003, 235, 225-231.	0.7	11
161	Monolithic cyan â˘" violet InGaN/GaN LED array. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600815.	0.8	11
162	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. Journal of Applied Physics, 2018, 123, 024304.	1.1	11

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163	High-pressure investigations of ferroelectric phase transition in PbGeTe. Journal of Physics C: Solid State Physics, 1984, 17, 2181-2192.	1.5	10
164	Metastable carrier concentration in GaAs/GaAlAs heterostructure under hydrostatic pressure. Journal of Applied Physics, 1988, 63, 2307-2310.	1.1	10
165	Novel trap state at the grain boundary: Metastable character of defects inpâ€HgMnTe andpâ€HgCdMnTe bicrystals. Journal of Applied Physics, 1989, 65, 1203-1207.	1.1	10
166	Angle Resolved Photoemission Spectroscopy of GaN (101-0): Experiment and Theory. Physica Status Solidi (B): Basic Research, 1999, 215, 751-755.	0.7	10
167	Electrical Properties of GaN Bulk Single Crystals Doped with Mg. Physica Status Solidi (B): Basic Research, 1999, 216, 567-570.	0.7	10
168	The role of oxygen and hydrogen in GaN. Physica B: Condensed Matter, 2001, 308-310, 117-121.	1.3	10
169	Dissociation of VGaâ€"ON complexes in HVPE GaN by high pressure and high temperature annealing. Physica Status Solidi (B): Basic Research, 2006, 243, 1436-1440.	0.7	10
170	Pressure-induced piezoelectric effects in near-lattice-matched GaN/AlInN quantum wells. Journal of Applied Physics, 2008, 104, 063505.	1.1	10
171	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. Journal of Applied Physics, 2012, 111, 033517.	1.1	10
172	Band gaps and built-in electric fields in InAlN/GaN short period superlattices: Comparison with (InAlGa)N quaternary alloys. Physical Review B, 2016, 93, .	1.1	10
173	Bandgap behavior of InGaN/GaN short period superlattices grown by metalâ€organic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2017, 254, 1600710.	0.7	10
174	Thermal conductivity of thin films of gallium nitride, doped with aluminium, measured with 3Ï‰ method. Solid State Sciences, 2020, 101, 106105.	1.5	10
175	Deformation Potential in High Electron Mobility GaAs/GaAsAs Heterostructures. Japanese Journal of Applied Physics, 1993, 32, 135.	0.8	9
176	Pressure Studies of Defects and Impurities in Nitrides. Physica Status Solidi (B): Basic Research, 1999, 216, 521-528.	0.7	9
177	Low dislocation density, high power InGaN laser diodes. MRS Internet Journal of Nitride Semiconductor Research, 2004, 9, 1.	1.0	9
178	Why InGaN laser-diode degradation is accompanied by the improvement of its thermal stability. Proceedings of SPIE, 2008, , .	0.8	9
179	Epitaxy of ternary nitrides on GaN single crystals. Journal of Crystal Growth, 1999, 198-199, 1061-1065.	0.7	8
180	Magnetic resonance studies of defects in GaN with reduced dislocation densities. Physica B: Condensed Matter, 2001, 308-310, 51-57.	1.3	8

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